

Silicon PNP Power Transistors

2SB695

DESCRIPTION

- With TO-3PN package
- Wide area of safe operation

APPLICATIONS

- For power amplifier and general purpose applications

PINNING

PIN	DESCRIPTION
1	Base
2	Collector;connected to mounting base
3	Emitter

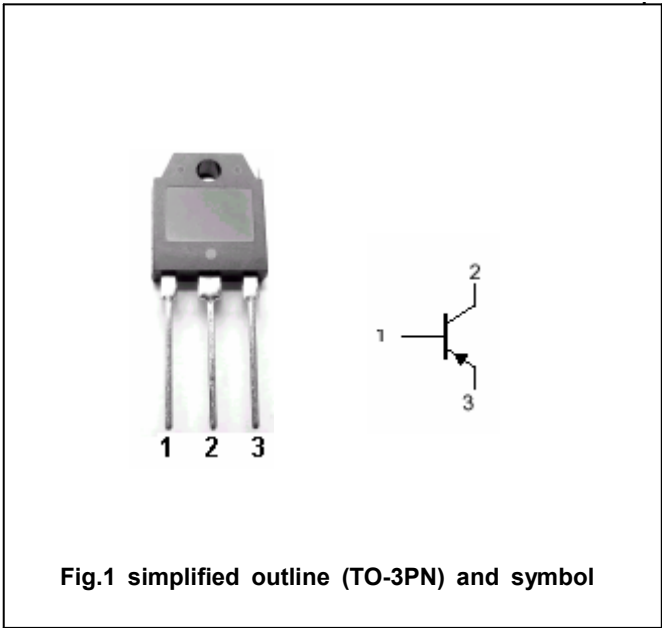


Fig.1 simplified outline (TO-3PN) and symbol

Absolute maximum ratings(Tc=25℃)

SYMBOL	PARAMETER	CONDITIONS	VALUE	UNIT
V _{CBO}	Collector-base voltage	Open emitter	-170	V
V _{CEO}	Collector-emitter voltage	Open base	-120	V
V _{EBO}	Emitter-base voltage	Open collector	-5	V
I _C	Collector current		-7	A
P _C	Collector power dissipation	T _C =25℃	80	W
T _j	Junction temperature		150	℃
T _{stg}	Storage temperature		-55~150	℃

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CHARACTERISTICS

Tj=25℃ unless otherwise specified

SYMBOL	PARAMETER	CONDITIONS	MIN	TYP.	MAX	UNIT
$V_{(BR)CEO}$	Collector-emitter breakdown voltage	$I_C=-30mA ; I_B=0$	-120			V
$V_{(BR)CBO}$	Collector-base breakdown voltage	$I_C=-1mA ; I_E=0$	-170			V
$V_{(BR)EBO}$	Emitter-base breakdown voltage	$I_E=-1mA ; I_C=0$	-5			V
V_{CEsat}	Collector-emitter saturation voltage	$I_C=-5A ; I_B=-0.5A$			-1.5	V
V_{BE}	Base-emitter on voltage	$I_C=-1A ; V_{CE}=-5V$			-1.5	V
I_{CBO}	Collector cut-off current	$V_{CB}=-170V ; I_E=0$			-50	μA
I_{EBO}	Emitter cut-off current	$V_{EB}=-5V ; I_C=0$			-50	μA
h_{FE-1}	DC current gain	$I_C=-1A ; V_{CE}=-5V$	40		200	
h_{FE-2}	DC current gain	$I_C=-5A ; V_{CE}=-5V$	20			
f_T	Transition frequency	$I_C=-1A ; V_{CE}=-5V$		7		MHz

PACKAGE OUTLINE

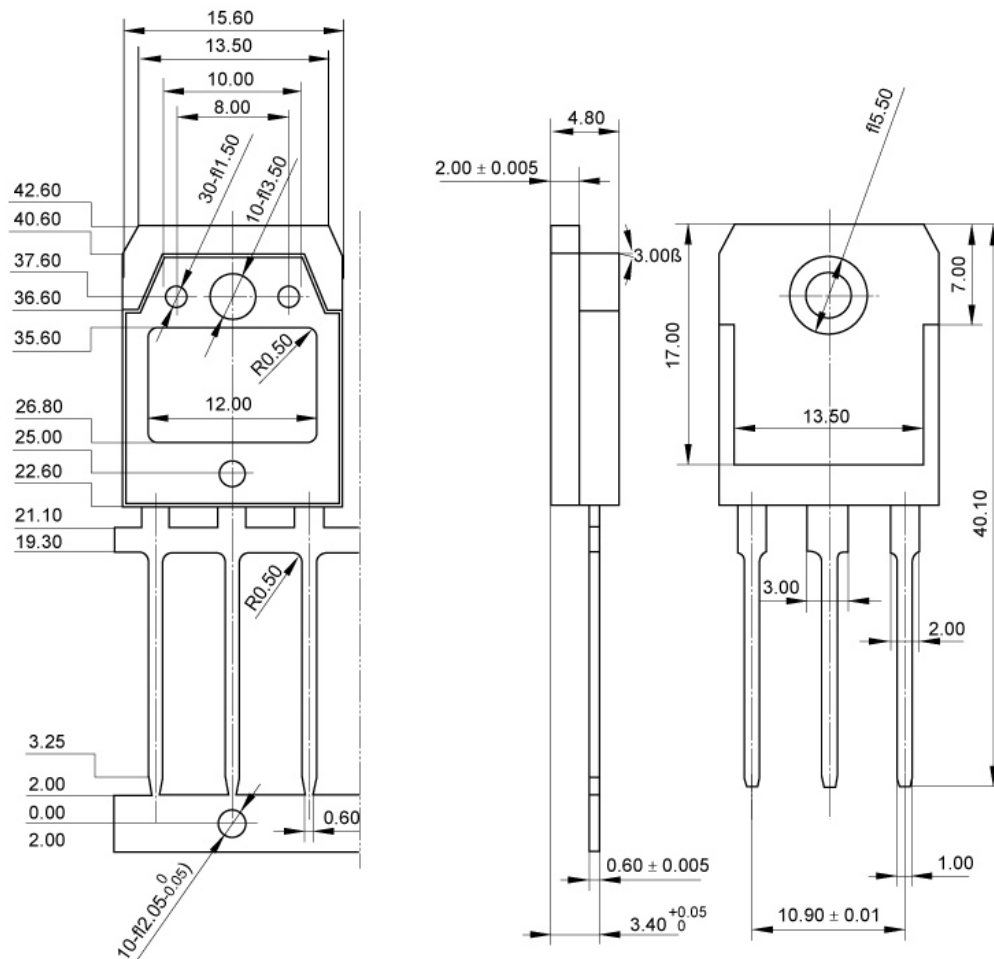


Fig.2 outline dimensions